

EUV Lithography

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EUV lithography (EUVL) is expected to be inserted for the 32 nm node, scheduled for 2012 according ITRS roadmap, and extended for the 22 nm and below. CEA-Leti is dealing with this new projection lithography technique since several years and presently in the framework of the European "More Moore" Project. This key note gives the basic concepts and current state of development of EUVL. First we provide an overview of the capabilities, the critical issues and challenges of EUVL. Then, we discuss more detailed topics like reflective mask specification, through binary and Phase Shift Mask (PSM), and some innovative technologies for mask defects reduction.

KEYNOTES